

1μm GaAs(680°C)

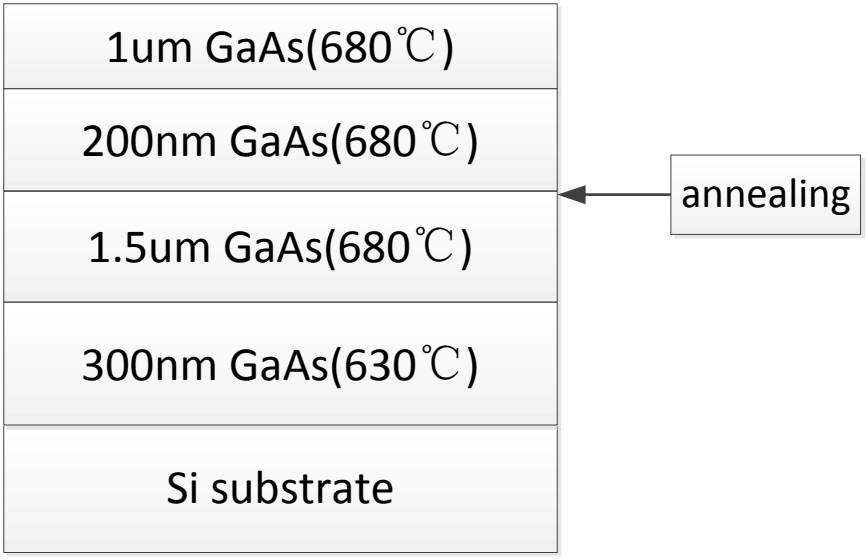
200nm GaAs(680°C)

1.5μm GaAs(680°C)

300nm GaAs(630°C)

Si substrate

annealing



The diagram shows a vertical stack of five layers. From top to bottom, they are: 1μm GaAs(680°C), 200nm GaAs(680°C), 1.5μm GaAs(680°C), 300nm GaAs(630°C), and Si substrate. An arrow points from a box labeled 'annealing' to the interface between the 200nm and 1.5μm GaAs layers.